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RLT92100G TECHNICAL DATA



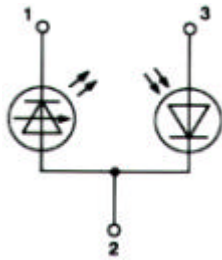
High Power Infrared Laserdiode

Structure: **AlGaAs/GaAs quantum well**
 Lasing wavelength: **920 nm typ., singlemode**
 Max. optical power: **110 mW, 1.5 x 3 μm² aperture**
 Package: **9 mm**

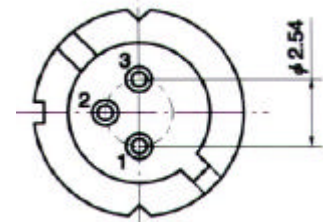
NOTE!
 LASERDIODE
 MUST BE COOLED!



PIN CONNECTION:



- 1) Laser diode cathode
- 2) Laser diode anode and photodiode cathode
- 3) Photodiode anode



Maximum Ratings (T_c=25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Optical Output Power	P _o	110	mW
LD Reverse Voltage	V _{R(LD)}	2	V
PD Reverse Voltage	V _{R(PD)}	30	V
Operating Temperature	T _C	-60 .. +60	°C
Storage Temperature	T _{STG}	-70 .. +85	°C

Optical-Electrical Characteristics (T_c = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN	TYP	MAX	UNIT
Optical Output Power	P _o	cw		100		mW
Threshold Current	I _{th}	cw		35		mA
Operation Current	I _{op}	P _o = 100 mW		200	240	mA
Operation Voltage	U _{op}	P _o = 100 mW		2.4		V
Lasing Wavelength	λ _p	P _o = 100 mW	915	920	925	nm
Beam Divergence	θ _∥	P _o = 100 mW	8	10	12	°
Beam Divergence	θ _⊥	P _o = 100 mW	30	35	40	°
Differential Efficiency	dP _o /dI _{op}	P _o = 100 mW	0.5	0.7	0.8	mW/mA
Monitor Current	I _m	P _o = 100 mW	0.2	0.4	1.3	mA